NPN Epitaxial Silicon Transistor

KSD1616A

Features

- Audio Frequency Power Amplifier and Medium Speed Switching
- Complement to KSB1116/KSB1116A
- These are Pb-Free Devices

ABSOLUTE MAXIMUM RATINGS

(Values are at T_A = 25°C unless otherwise noted.)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	120	V
V _{CEO}	Collector-Emitter Voltage	60	V
V _{EBO}	Emitter-Base Voltage	6	V
I _C	Collector Current (DC)	1	Α
I _{CP}	Collector Current (Pulse) (Note 1)	2	Α
T _J	Junction Temperature	150	°C
T _{STG}	Storage Temperature	-55 to 150	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

1. Pulse width ≤ 10 ms, duty cycle < 50%.

THERMAL CHARACTERISTICS

(Values are at T_A = 25°C unless otherwise noted.)

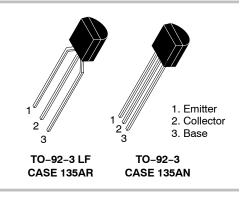
Symbol	Parameter	Max	Unit
P _D	Total Device Dissipation	0.75	W
	Derate Above 25°C	6	mW/°C
$R_{ heta JA}$	Thermal Resistance, Junction-to-Ambient	160	°C/W

2. PCB size: FR-4, 76 mm \times 114 mm \times 1.57 mm (3.0 inch \times 4.5 inch \times 0.062 inch) with minimum land pattern size.

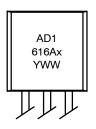


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MARKING DIAGRAM



= Assembly Location D1616Ax = Specific Device Code

x = G or Y

= Year of Production WW = Work Week Number

ORDERING INFORMATION

Device	Package	Shipping
KSD1616AGBU	TO-92-3 (Pb-Free)	10,000 Units / Bulk Bag
KSD1616AGTA	TO-92-3 LF (Pb-Free)	2,000 Units / Fan-Fold
KSD1616AYTA	TO-92-3 LF (Pb-Free)	2,000 Units / Fan-Fold

KSD1616A

ELECTRICAL CHARACTERISTICS

(Values are at $T_A = 25^{\circ}C$ unless otherwise noted.)

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
BV _{CBO}	Collector-Base Breakdown Voltage	$I_C = 100 \mu A, I_E = 0$	120	-	-	V
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 1 mA, I _B = 0	60	-	-	V
BV _{EBO}	Emitter-Base Breakdown Voltage	$I_E = 100 \mu A, I_C = 0$	6	-	-	V
I _{CBO}	Collector Cut-Off Current	V _{CB} = 60 V, I _E = 0	-	-	100	nA
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 6 V, I _C = 0	-	-	100	nA
h _{FE1}	DC Current Gain	V _{CE} = 2 V, I _C = 100 mA	135	-	400	
h _{FE2}	DC Current Gain	V _{CE} = 2 V, I _C = 1 A	81	-	-	
V _{BE(on)}	Base-Emitter On Voltage (Note 3)	$V_{CE} = 2 \text{ V}, I_{C} = 50 \text{ mA}$	600	640	700	mV
V _{CE(sat)}	Collector–Emitter Saturation Voltage (Note 3)	I _C = 1 A, I _B = 50 mA	-	0.15	0.30	V
V _{BE(sat)}	Base–Emitter Saturation Voltage (Note 3)	I _C = 1 A, I _B = 50 mA	-	0.9	1.2	V
C _{ob}	Output Capacitance	V _{CE} = 10 V, I _E = 0, f = 1 MHz	-	19	-	pF
f _T	Current Gain Bandwidth Product	V _{CE} = 2 V, I _C = 100 mA	100	160	-	MHz
t _{ON}	Turn-On Time	V_{CC} = 10 V, I_{C} = 100 mA, I_{B1} = $-I_{B2}$ = 10 mA, $V_{BE(off)}$ = -2 V ~ -3 V	-	0.07	=	μs
t _{STG}	Storage Time		-	0.95	-	μs
t _F	Fall Time		-	0.07	-	μs

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions. 3. Pulse test: pulse width < 350 μ s, duty cycle \leq 2% pulsed.

$h_{\mbox{\scriptsize FE}}$ CLASSIFICATION

Classification	Y	G
hFE1	135 ~ 270	200 ~ 400

KSD1616A

TYPICAL PERFORMANCE CHARACTERISTICS

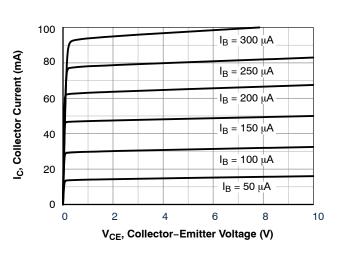


Figure 1. Static Characteristic

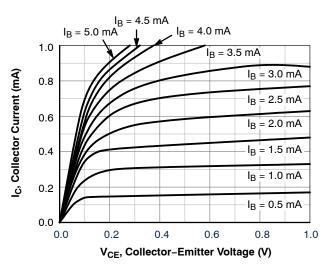


Figure 2. Static Characteristic

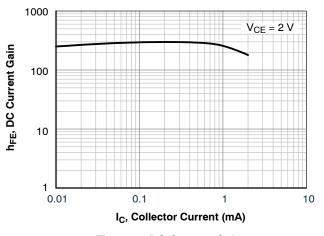


Figure 3. DC Current Gain

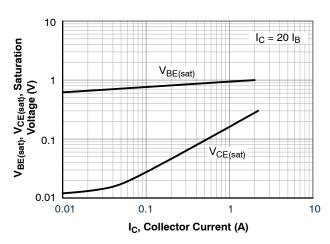


Figure 4. Base–Emitter Saturation Voltage and Collector–Emitter Saturation Voltage

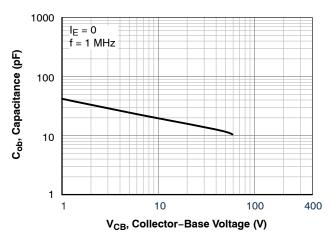


Figure 5. Collector Output Capacitance

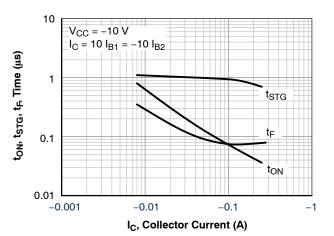


Figure 6. Switching Time

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TYPICAL CHARACTERISTICS (continued)

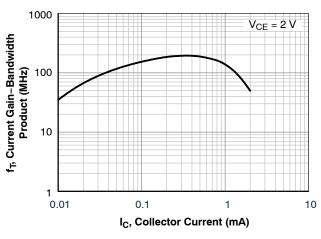


Figure 7. Current Gain Bandwidth Product

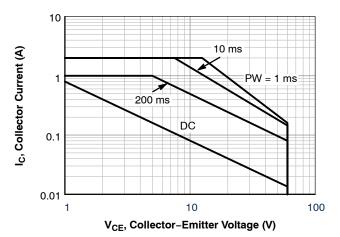


Figure 8. Safe Operating Area

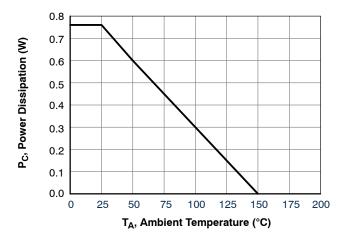
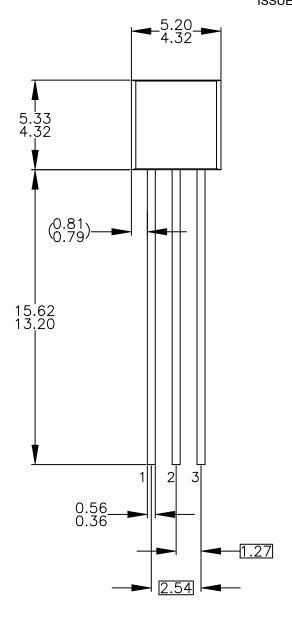
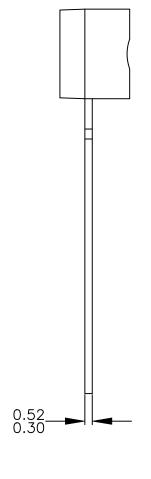


Figure 9. Power Derating

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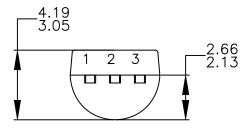
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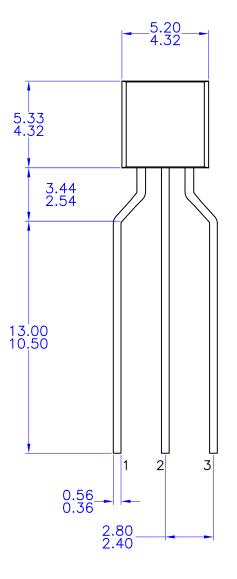
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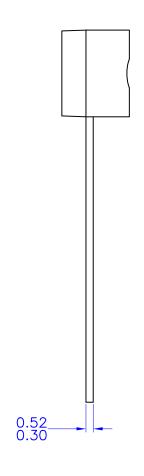
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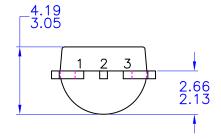
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